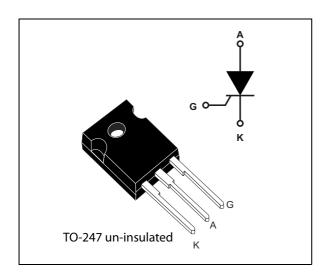




50 A 1200 V automotive grade SCR

Datasheet - production data



Features

On-state current: 50 A rms
Blocking voltage: 1200 V

· High static and dynamic commutation:

 $- dI/dt = 200 A/\mu s$ - $dV/dt = 1000 V/\mu s$

AEC-Q101I_{GT} = 50 mA

• ECOPACK®2 compliant component

Applications

- Automotive:
 - on board, off board battery charger
- · Solar, wind renewable energy inverters
- Solid state relay
- UPS:
 - Bypass
 - ICL (inrush current limiter)
 - Battery charger
- · Industrial welding systems
- Voltage control rectifier

Description

Available in TO-247 high power package, the TN5050H-12WY autograde is suitable in applications such as automotive / stationary battery charger, renewable energy generator, interruptible power supply, solid state relay, welding equipment and motor drive applications. Its power switching, voltage robustness and power dissipation performances are the key features for functions such as a 80 A AC switch, an AC phasing inverter and an AC-DC controlled rectifier bridge.

The TN5050H-12WY is an automotive grade product and offers a superior performance in surge current handling, thermal cooling capabilities and overvoltage robustness.

Table 1. Device summary

Symbol	Value	Unit
I _{T(RMS)}	50	А
V_{DRM}, V_{RRM}	1200	V
V_{DSM}, V_{RSM}	1300	V
I _{GT}	50	mA
Tj	150	°C

Characteristics TN5050H-12WY

1 Characteristics

Table 2. Absolute ratings (limiting values, $T_j = 25$ °C unless otherwise stated)

Symbol	Parameter	Value	Unit		
V_{DRM}/V_{RMM}	Repetitive off-state voltage (50-60 Hz)	T _j = 150 °C	1200	V	
I _{T(RMS)}	On-state rms current (180° conduction angle)		T _c = 137 °C	50	Α
I _{T(AV)}	Average on-state current (180° conduction angle)		1 _C = 137 C	32	A
I _{T(RMS)}	On-state rms current (180° conduction angle)		T = 125 °C	80	Α
I _{T(AV)}	Average on-state current (180° conduction angle)		T _c = 125 °C	51	^
I _{TSM} ⁽¹⁾	Non repetitive surge peak on-state current (1; initial = 25 °C)		$t_p = 8.3 \text{ ms}$	633	Α
TSM`			t _p = 10 ms	580	^
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$ $F = 50 \text{ Hz}$		T _j = 150 °C	200	A/µs
I _{GM}	Forward peak gate current $T_j = 150 ^{\circ}\text{C}$		t _p = 20 μs	8	Α
P _{G(AV)}	Average gate power dissipation $T_j =$			1	W
T _{stg}	Storage junction temperature range			- 40 to + 150	°C
T _j	Operating junction temperature range			- 40 to + 150	°C

^{1.} ST recommends I²t value for fusing = 1680 A²s for T_j = 25 °C and T_p = 10 ms.

TN5050H-12WY Characteristics

Table 3. Electrical characteristics ($T_i = 25$ °C, unless otherwise specified)

Symbol	Test conditions			Value	Unit
1	$V_D = 12 \text{ V}, R_L = 33 \Omega$		Min.	10	mA
I _{GT}			Max.	50	1 IIIA
V _{GT}	$V_D = 12 \text{ V}, R_L = 33 \Omega$		Max.	1	V
$V_{\sf GD}$	$V_D = 2/3 \text{ X } V_{DRM}, R_L = 3.3 \text{ k } \Omega$	T _j = 150 °C	Min.	0.15	V
I _H	I _T = 500 mA, gate open			100	mA
ΙL	I _G = 1.2 X I _{GT}			125	mA
t _{gt}	$I_T = 50 \text{ A}, V_D = V_{DRM}, I_G = 200 \text{ mA}, dI_G/dt = 0.2 \text{ A/}\mu\text{s}$			3	μs
dV/dt	$V_D = 2/3 \text{ X } V_{DRM}$, gate open $T_j = 150 \text{ °C}$		Min.	1000	V/µs
t _q	$\begin{aligned} & I_T = 33 \text{ A, V}_D = 800 \text{ V, V}_R = 75 \text{ V, t}_P = 100 \mu\text{s, d} \\ & dV_D/dt = 20 \text{ V/}\mu\text{s} \end{aligned} \qquad T_j = 150 ^{\circ}\text{C}$		Тур	150	μs
V _{TM}	I _{TM} = 100 A, t _P = 380 μs		Max.	1.55	V
V _{TO}	Threshold voltage	T _j = 150 °C	Max.	0.88	V
R _D	Dynamic resistance $T_j = 150 ^{\circ}\text{C}$		Max.	6	mΩ
		T _j = 25 °C	Max.	5	μA
I _{DRM/} I _{RRM}	$V_D = V_{DRM}, V_R = V_{RRM}$	T _j = 125 °C	Max.	3	mA
	$T_j = 1$		Max.	7.5	mA
I _{DSM/} I _{RSM}	$V_D = V_{DSM}, V_R = V_{RSM}$	T _j = 25 °C	Max.	10	μΑ

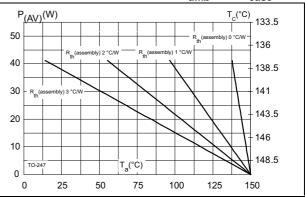
Table 4. Thermal resistance

Symbol	Parameter	Value	Unit	
R _{th(j-c)}	Junction to case (DC)	TO-247	0.3	°C/W
R _{th(j-a)}	Junction to ambient	10-247	50	°C/W

Figure 1. Maximum average power dissipation versus average on-state current

P(W) 55 50 45 DC α = 120 40 α = 90 35 α = 60 30 α = 30 25 20 15 360° 10 15 20 25

Figure 2. Correlation between maximum average power dissipation and maximum allowable temperatures (T_{amb} and T_{case})



Characteristics TN5050H-12WY

Figure 3. Average and D.C. on-state current versus case temperature

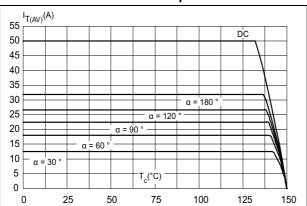


Figure 4. Average and D.C. on-state current versus ambient temperature

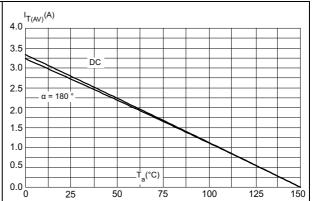


Figure 5. Relative variation of thermal impedance junction to case and junction to ambient versus pulse duration

1.0E-01

1.0E-02

1.0E-03

1.0E-03

1.0E-02

1.0E-03

1.0E-01

1.0E-01

1.0E-02

1.0E-03

1.0E-02

1.0E-03

1.0E-03

1.0E-03

1.0E-04

1.0E-05

1.0E-05

1.0E-06

1.0E-07

1.0E-08

Figure 6. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

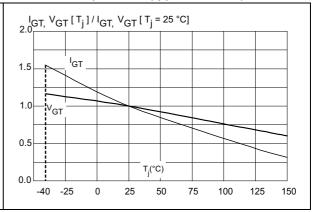


Figure 7. Relative variation of holding and latching current versus junction temperature (typical values)

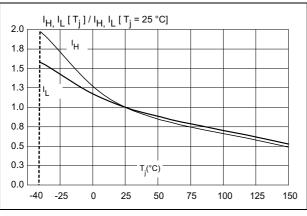
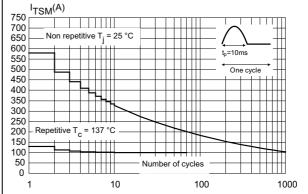


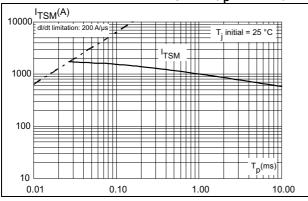
Figure 8. Surge peak on-state current versus number of cycles



TN5050H-12WY Characteristics

Figure 9. Non repetitive surge peak on-state current for a sinusoidal pulse ($t_p < 10 \text{ ms}$)

Figure 10. On-state characteristics (maximum values)



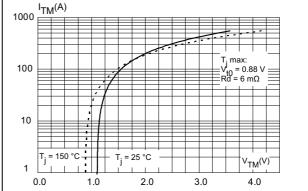
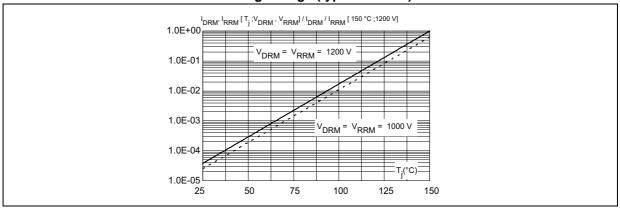


Figure 11. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)



Package information TN5050H-12WY

2 Package information

- Epoxy meets UL94, V0
- Lead-free package

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Heat-sink plane

B

C

A

Heat-sink plane

ØP

L2

Back view

Figure 12. TO-247 dimension definitions

Table 5. TO-247 dimension values

			Dime	nsions		
Ref.		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур	Max.
А	4.85		5.15	0.191		0.203
A1	2.20		2.60	0.086		0.102
b	1.00		1.40	0.039		0.055
b1	2.00		2.40	0.078		0.094
b2	3.00		3.40	0.118		0.133
С	0.40		0.80	0.015		0.031
D ⁽¹⁾	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
е	5.30	5.45	5.60	0.209	0.215	0.220
L	14.20		14.80	0.559		0.582
L1	3.70		4.30	0.145		0.169
L2		18.50 typ.			0.728 typ.	
ØP ⁽²⁾	3.55		3.65	0.139		0.143
ØR	4.50		5.50	0.177		0.217
S	5.30	5.50	5.70	0.209	0.216	0.224

^{1.} Dimension D plus gate protrusion does not exceed 20.5 mm

^{2.} Resin thickness around the mounting hole is not less than 0.9 \mbox{mm}

Ordering information TN5050H-12WY

3 Ordering information

Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
TN5050H-12WY	TN5050H12Y	TO-247	4.43 g	30	Tube

4 Revision history

Table 7. Document revision history

Date	Revision	Changes
07-Jan-2015	1	Initial release.

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